

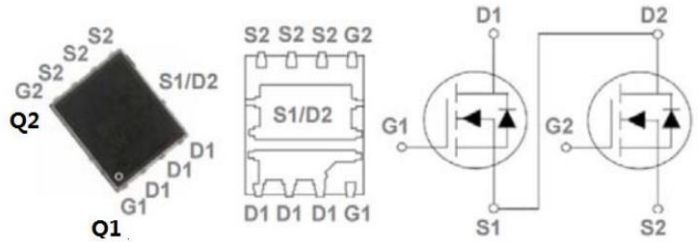
Features

- Low $R_{DS(on)}$ @ $V_{GS}=10V$
- 100% UIS Tested
- Pb-Free, RoHS Compliant

$V_{(BR)DSS}$	$R_{DS(on)}$ Typ	I_D Max
40V	10mΩ @10V	30A
	18mΩ @4.5V	

Applications

- Load Switch
- Switching Circuits
- High Speed line Driver
- Power management



TDFN3X3

Order Information

Product	Package	Marking	Packing
SIZ320DT-T1-GE3-CN	TDFN3X3	4466	3000PCS/Reel

Absolute Maximum Ratings

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Symbol	Parameter	Rating	Unit	
Common Ratings (TA=25°C Unless Otherwise Noted)				
V_{GS}	Gate-Source Voltage	±20	V	
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	40	V	
T_J	Maximum Junction Temperature	150	°C	
T_{STG}	Storage Temperature Range	-50 to 150	°C	
Mounted on Large Heat Sink				
I_{DM}	Pulse Drain Current Tested①	$T_A=25°C$	120	A
I_D	Continuous Drain Current	$T_A=25°C$	30	A
		$T_A=70°C$	24	
P_D	Maximum Power Dissipation	$T_A=25°C$	26	W
EAS	Avalanche energy, single pulsed ②		29	
$R_{\theta JC}$	Thermal Resistance Junction-Ambient		4.8	°C/W

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ T_J = 25°C (unless otherwise stated)						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V I _D =250μA	40	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current(T _A =25°C)	V _{DS} =40V, V _{GS} =0V	-	-	1	μA
	Zero Gate Voltage Drain Current(T _A =125°C)	V _{DS} =32V, V _{GS} =0V	-	-	100	nA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.2	1.6	2.5	V
R _{DS(ON)}	Drain-Source On-State Resistance②	V _{GS} =10, I _D =4A	-	10	13	mΩ
R _{DS(ON)}	Drain-Source On-State Resistance②	V _{GS} =4.5V, I _D =3A	-	18	22	mΩ
Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise stated)						
C _{iss}	Input Capacitance	V _{DS} =20V, V _{GS} =0V, f=1MHz	-	407	-	pF
C _{oss}	Output Capacitance		-	195	-	pF
C _{rss}	Reverse Transfer Capacitance		-	7.7	-	pF
Q _g	Total Gate Charge	V _{DS} =20V I _D =15A, V _{GS} =10V	-	6.9	-	nC
Q _{gs}	Gate Source Charge		-	1.3	-	nC
Q _{gd}	Gate Drain Charge		-	3.0	-	nC
Switching Characteristics						
t _{d(on)}	Turn on Delay Time	V _{DD} =20V, I _D =1A, R _G =3.3Ω, V _{GS} =10V	-	17.2	-	ns
t _r	Turn on Rise Time		-	29.6	-	ns
t _{d(off)}	Turn Off Delay Time		-	46.8	-	ns
t _f	Turn Off Fall Time		-	34.6	-	ns
Source Drain Diode Characteristics						
I _{SD}	Source drain current(Body Diode)	T _A =25°C	-	-	2	A
V _{SD}	Forward on voltage②	T _J =25°C, I _{SD} =4A, V _{GS} =0V	-	0.84	1.2	V

Notes:

① Pulse width limited by maximum allowable junction temperature

② Pulse test ; Pulse width≤300μs, duty cycle≤2%.

Typical Characteristics

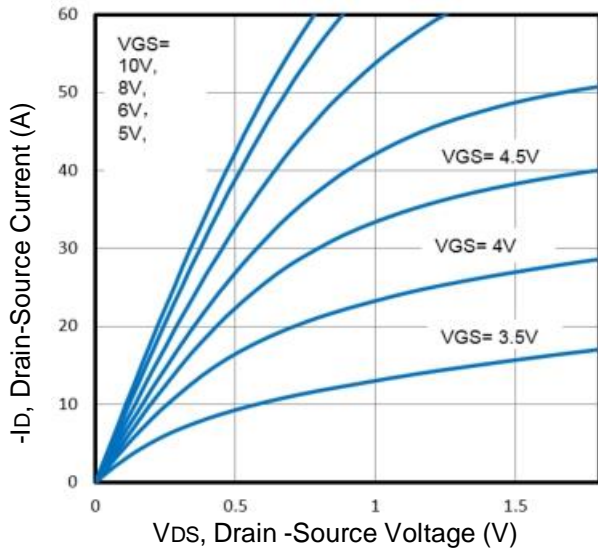


Fig1. Typical Output Characteristics

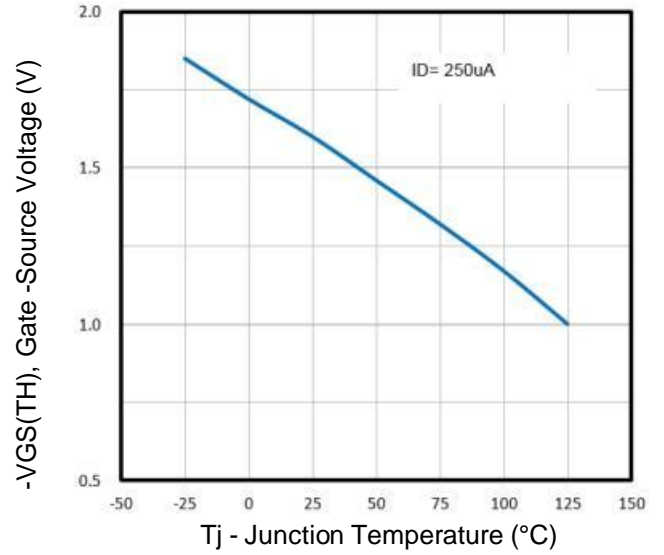


Fig2. Normalized Threshold Voltage Vs. Temperature

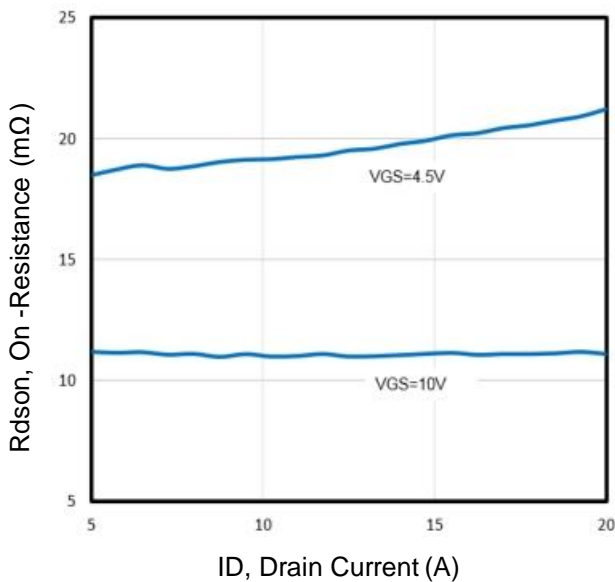


Fig3. On-Resistance vs. Drain Current and Gate

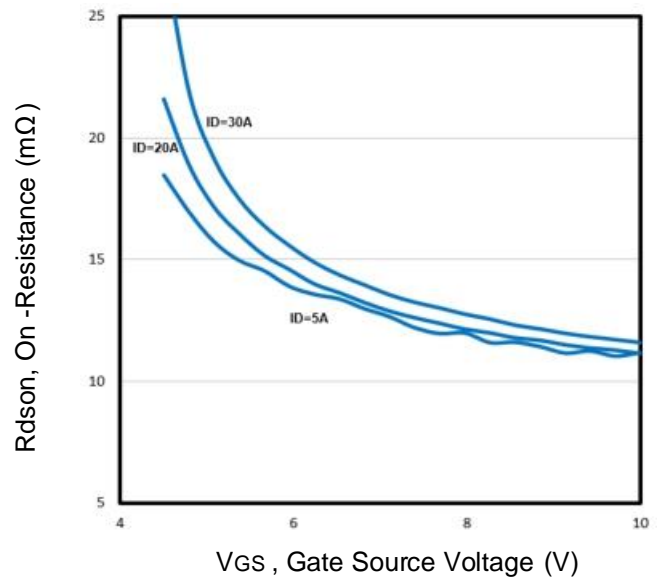
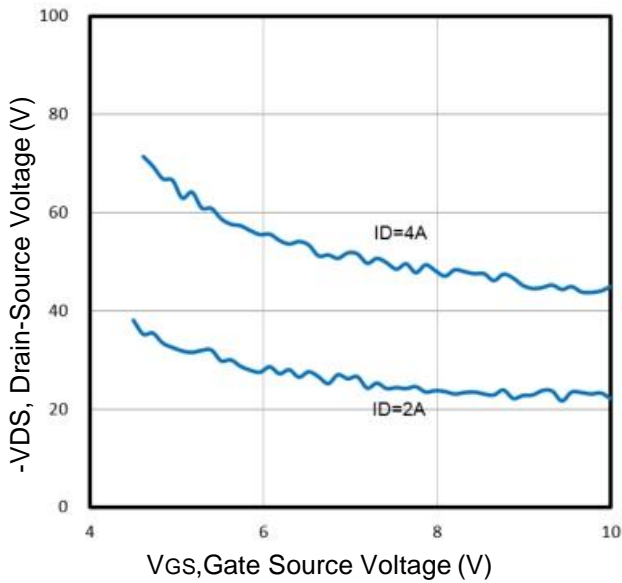
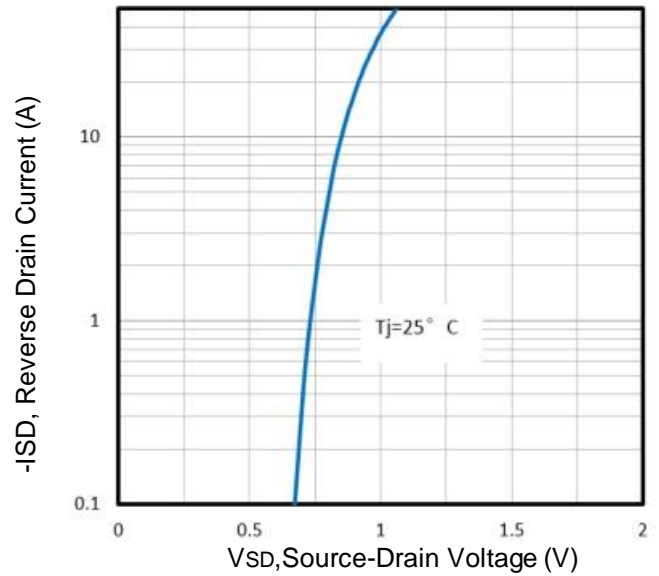
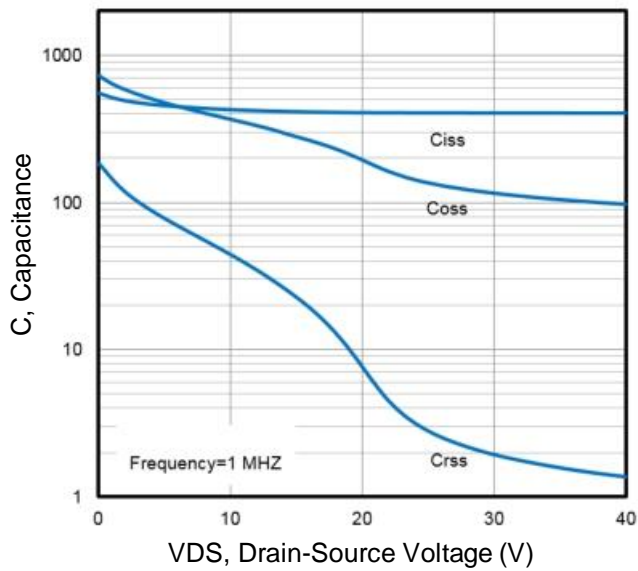
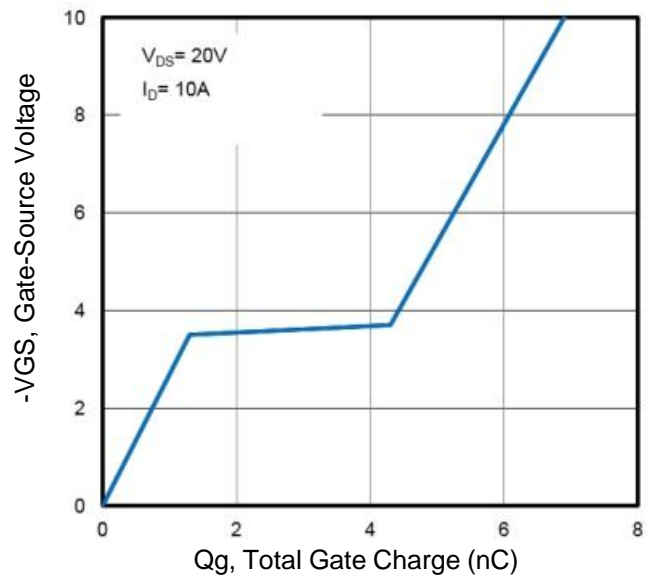
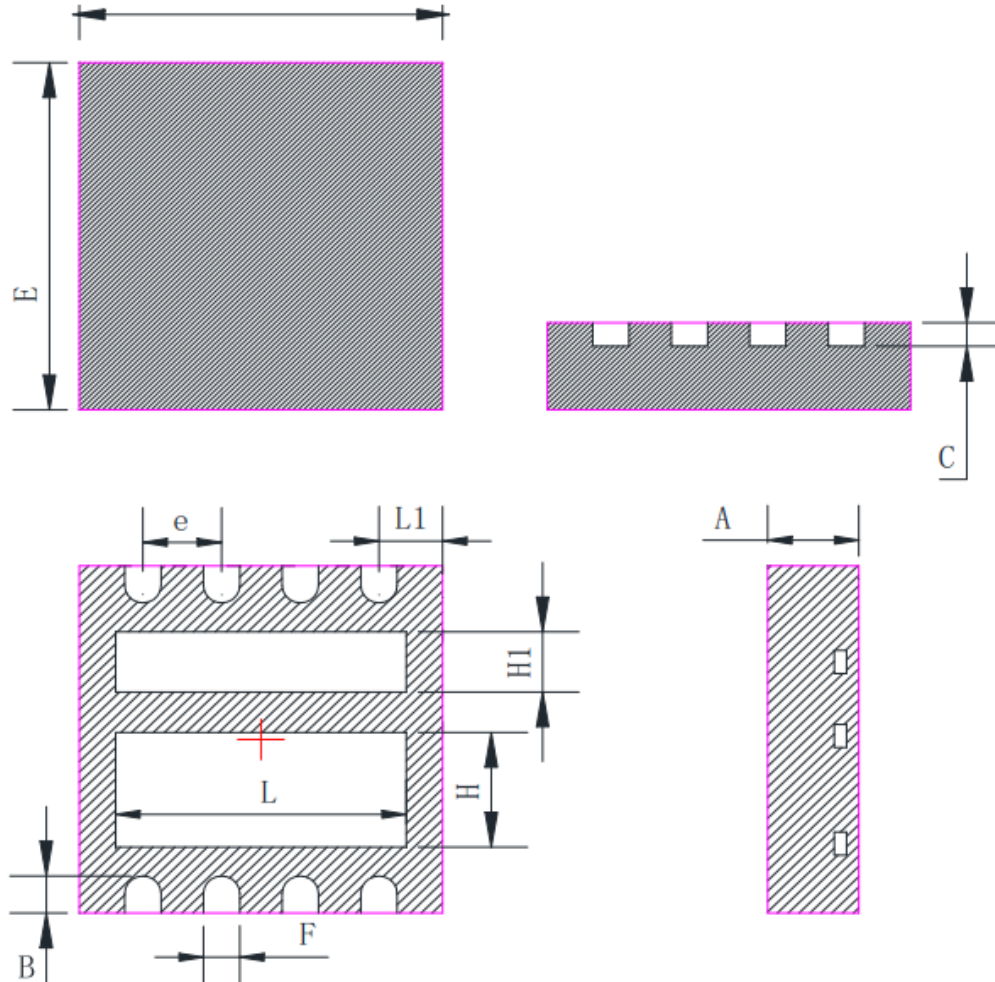


Fig4. On-Resistance vs. Gate Source Voltage

Typical Characteristics

Fig5. Drain-Source Voltage vs Gate-Source Voltage

Fig6. Typical Source-Drain Diode Forward Voltage

Fig7. Typical Capacitance Vs. Drain-Source Voltage

Fig8. Typical Gate Charge Vs. Gate-Source Voltage

TDFN3X3 Mechanical Data


Symbol	Min	Typ	Max
A	0.70	0.75	0.80
B	0.27	0.32	0.37
C	0.153	0.203	0.253
D	2.90	3.00	3.10
E	2.90	3.00	3.10
e	0.60	0.65	0.70
F	0.25	0.30	0.35
H	0.89	0.99	1.09
H1	0.42	0.52	0.62
L	2.30	2.40	2.50
L1	0.425	0.525	0.625

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